



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
30V	3.2m Ω @ $V_{GS} = 10V$	100A
	5.5m Ω @ $V_{GS} = 4.5V$	85A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

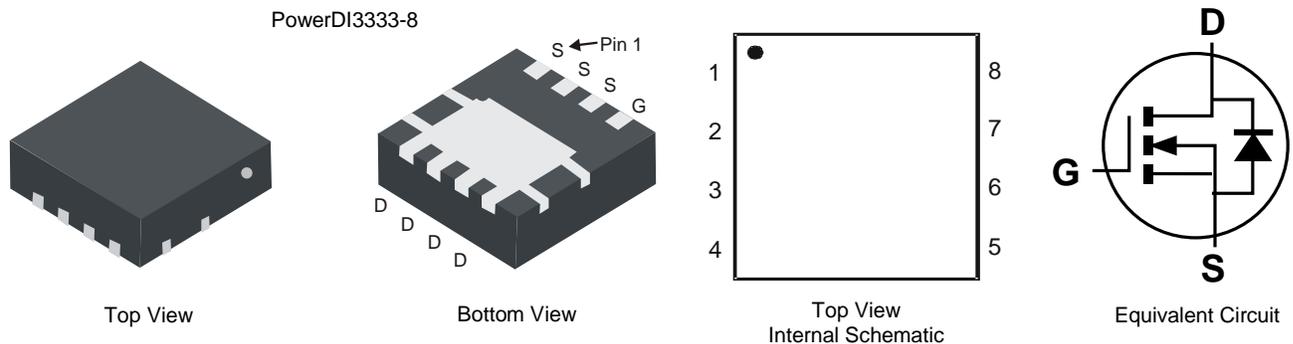
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Excellent $Q_{GD} \times R_{DS(ON)}$ Product (FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.008 grams (Approximate)



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V_{GSS}	± 20	V	
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	I_D	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	100 90	A
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$		$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	22 18	A
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	3	A	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	100	A	
Avalanche Current, L=1mH	I_{AS}	16	A	
Avalanche Energy, L=1mH	E_{AS}	250	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	2.4	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52	$^\circ\text{C/W}$
Total Power Dissipation (Note 5)	P_D	$T_C = +25^\circ\text{C}$	62	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	2	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$	

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = +20\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = -16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.4	3.2	m Ω	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	4	5.5		$V_{GS} = 4.5\text{V}, I_D = 15\text{A}$
Diode Forward Voltage	V_{SD}	—	0.75	1	V	$V_{GS} = 0\text{V}, I_S = 10\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	—	2,370	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{OSS}	—	1,360	—		
Reverse Transfer Capacitance	C_{RSS}	—	240	—		
Gate Resistance	R_G	—	0.6	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_G	—	20	—	nC	$V_{DS} = 15\text{V}, I_D = 20\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_G	—	44	—		
Gate-Source Charge	Q_{GS}	—	7	—		
Gate-Drain Charge	Q_{GD}	—	8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.2	—	ns	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_L = 0.75\Omega, R_G = 3\Omega, I_D = 20\text{A}$
Turn-On Rise Time	t_R	—	4.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	21	—		
Turn-Off Fall Time	t_F	—	8	—		
Body Diode Reverse Recovery Time	t_{RR}	—	25	—	ns	$I_F = 15\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	37	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

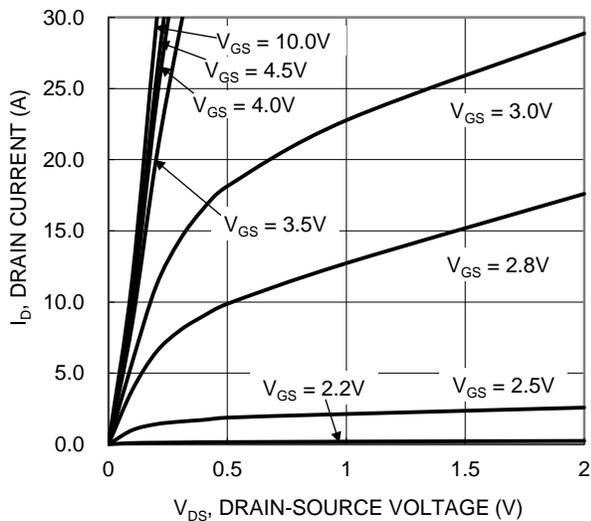


Figure 1. Typical Output Characteristic

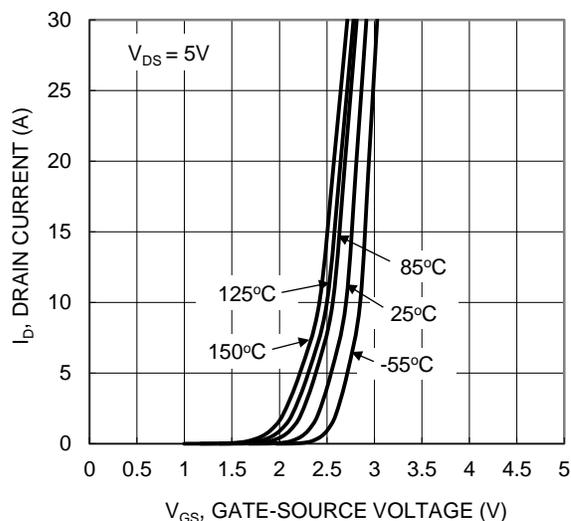


Figure 2. Typical Transfer Characteristic

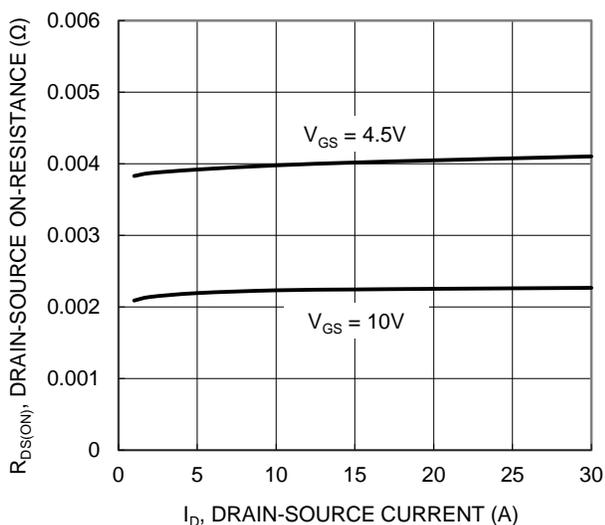


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

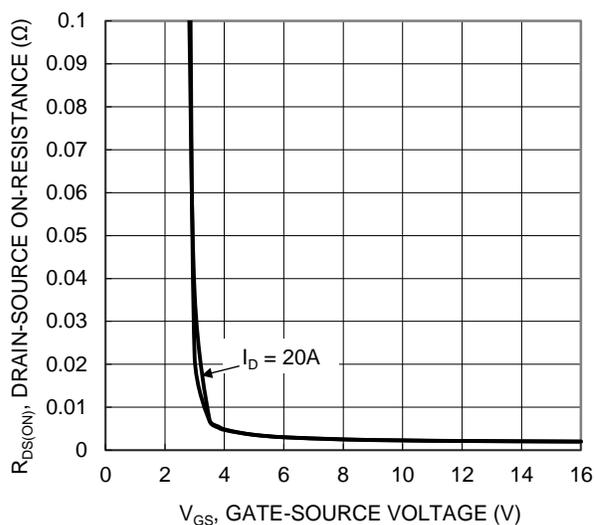


Figure 4. Typical Transfer Characteristic

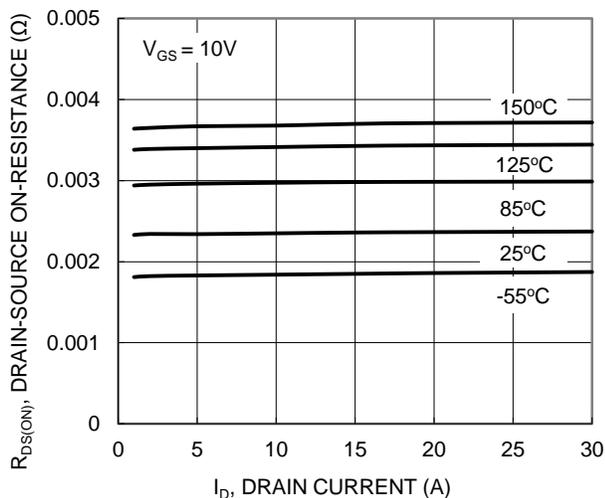


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

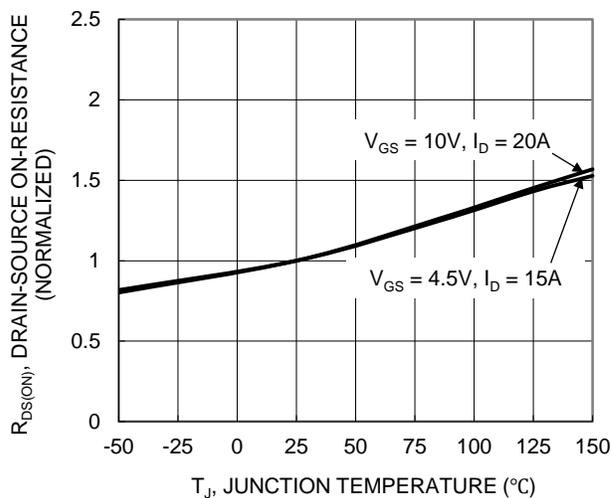


Figure 6. On-Resistance Variation with Junction Temperature

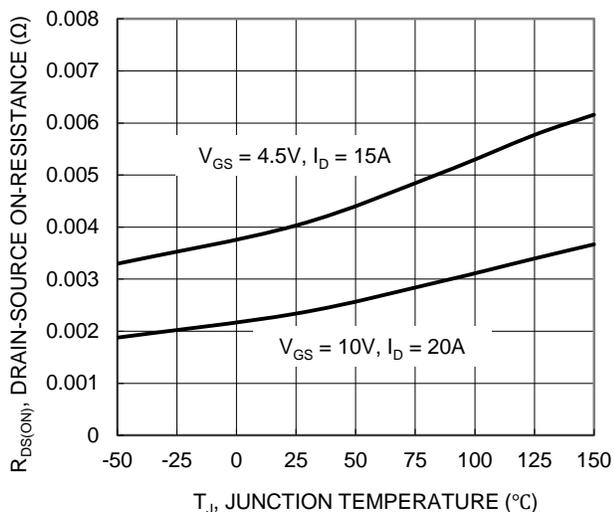


Figure 7. On-Resistance Variation with Junction Temperature

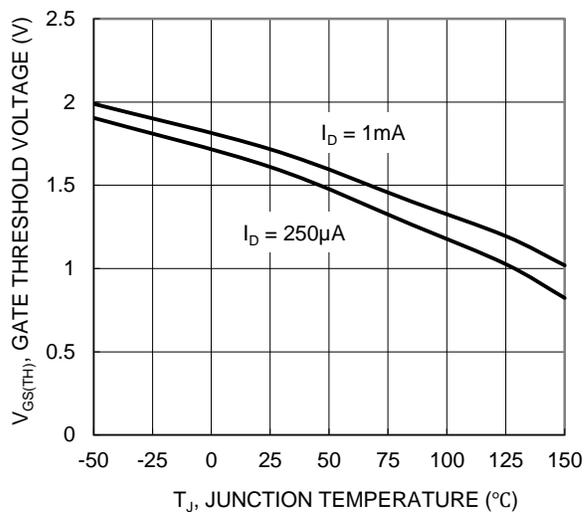


Figure 8. Gate Threshold Variation vs. Junction Temperature

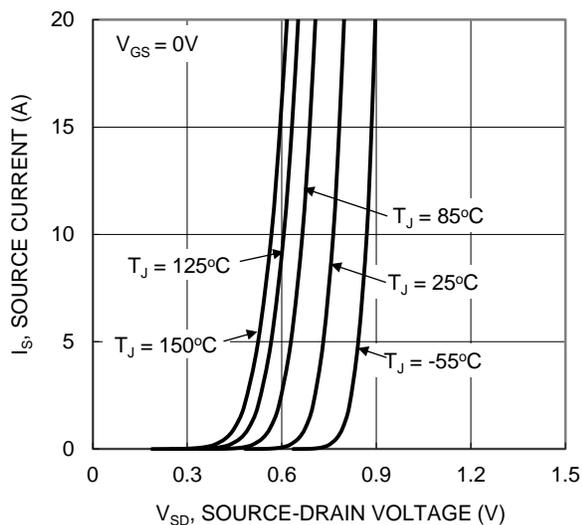


Figure 9. Diode Forward Voltage vs. Current

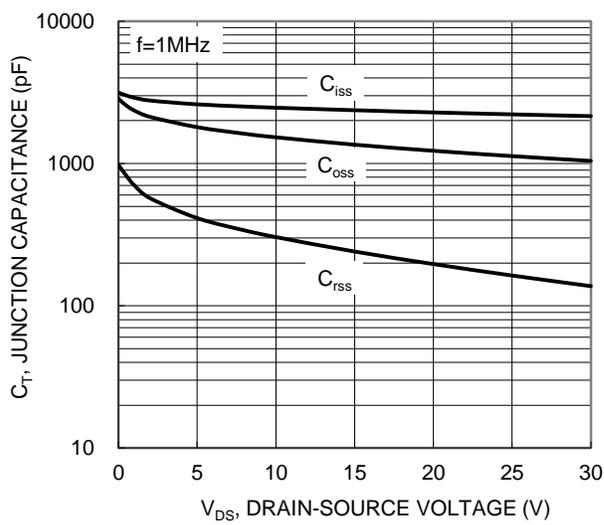


Figure 10. Typical Junction Capacitance

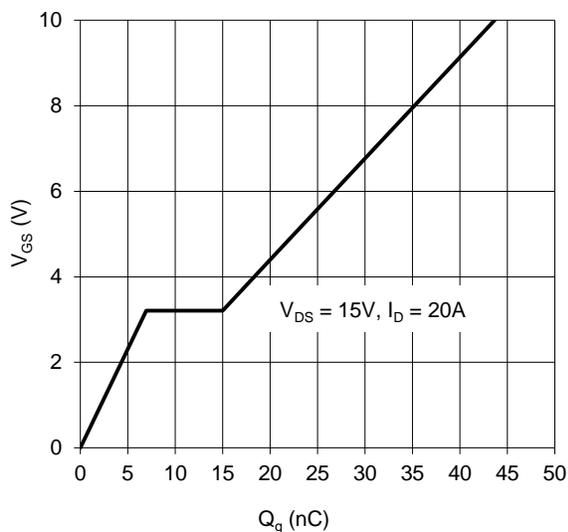


Figure 11. Gate Charge

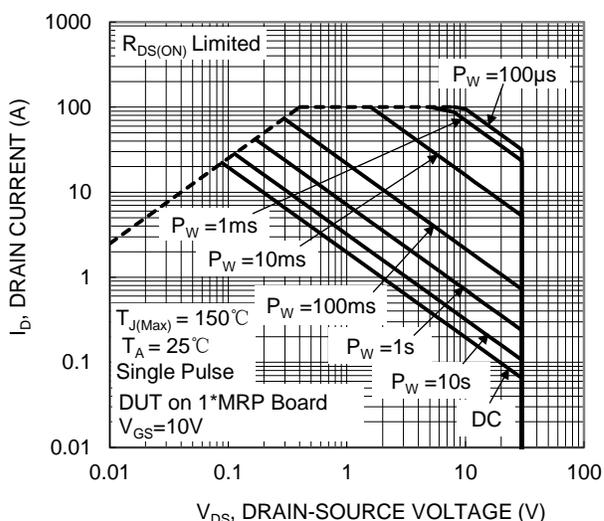


Figure 12. SOA, Safe Operation Area

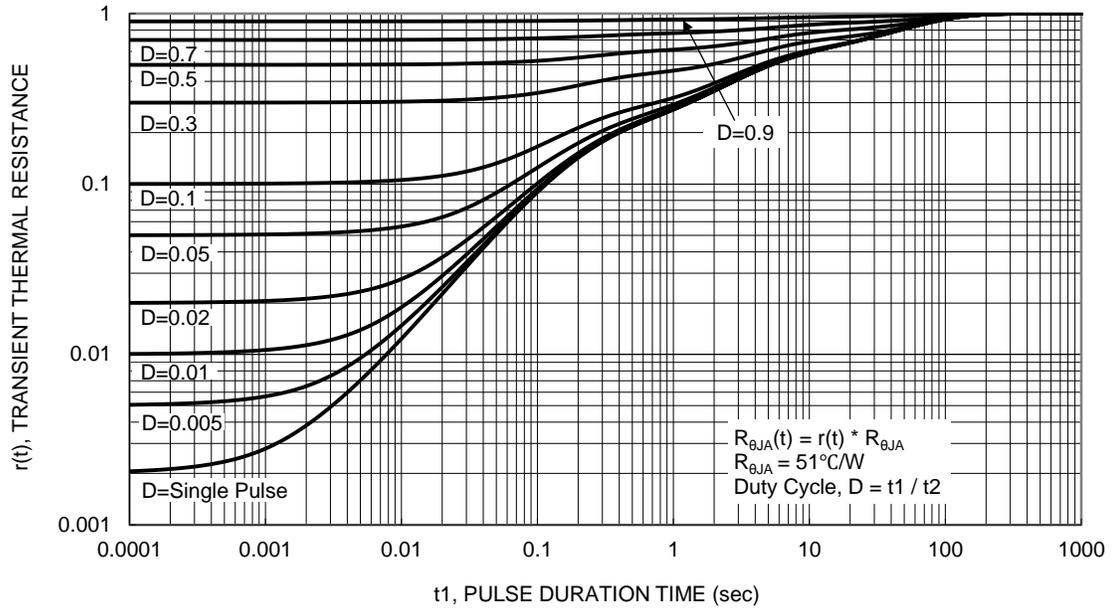
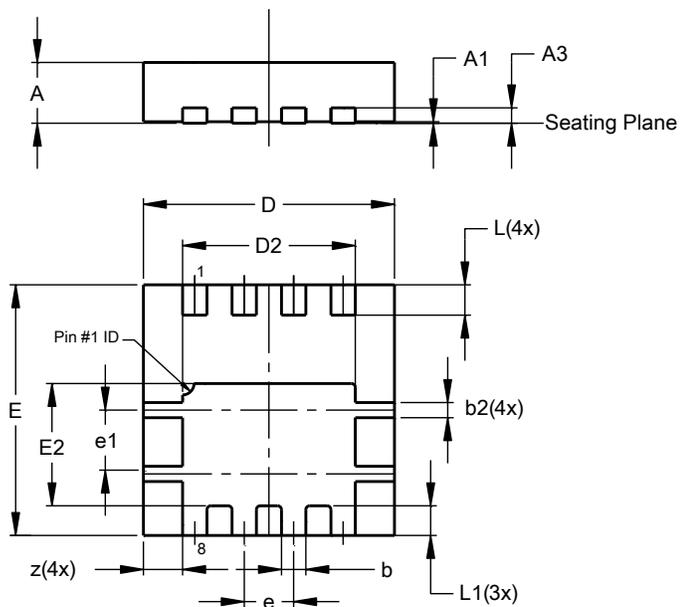


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

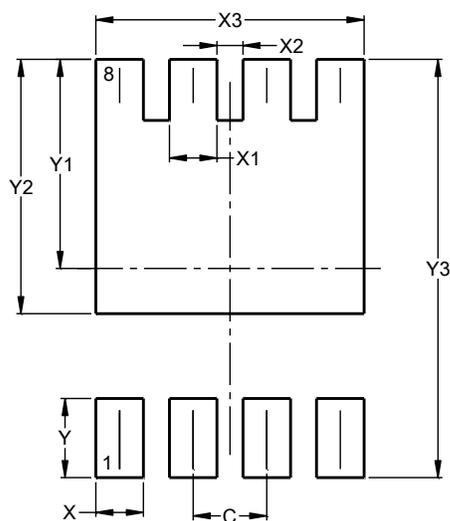
PowerDI3333-8



PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	-	-	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700